

Parameter	Tr1 and Tr2
V_{CEO}	20V
V_{EBO}	12V
I _C	600mA
R_1	10kΩ

SMT6 (4) (5) (6) (1)

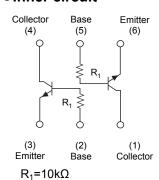
SOT-457 (SC-74)

Outline

Features

- 1) Built-In Biasing Resistors
- 2) Two DTC614T chips in one package.
- 3) Low saturation voltage, typically $V_{CE(sat)}$ =40mV at I_C / I_B =50mA / 2.5mA, makes these transistors ideal for muting circuits.
- 4) These transistors can be used at high current levels, $I_{\rm C}$ =600mA.
- 5) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 6) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 7) Lead Free/RoHS Compliant.

●Inner circuit



Application

Muting circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
IMH21	SMT6	2928	T110	180	8	3,000	H21

●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V_{EBO}	12	V
Callegator accurant	I _C	600	mA
Collector current	I _{CP} *1	1	А
Power dissipation	P_D^{*2}	300(Total) *3	mW
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55 to +150	

●Electrical characteristics (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	20	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	20	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	12	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 20V	1	1	0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 12V	ı	ı	0.5	μΑ
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C}$ / $I_{\rm B}$ = 50mA / 2.5mA	ı	40	150	mV
DC current gain	h _{FE}	V_{CE} = 5V, I_{C} = 50mA	820	ı	2700	-
Input resistance	R ₁	-	7	10	13	kΩ
Transition frequency	f _T *4	V _{CE} = 10V, I _E = -50mA f = 100MHz	-	150	1	MHz
Output ON Resistance	R _{on}	$V_1 = 5V$ $R_L = 1k\Omega, f = 1kHz$	-	0.9	-	Ω

^{*1} P_W=10ms, Single pulse

^{*2} Each terminal mounted on a reference footprint

^{*3 200}mW per element must not be exceeded.

^{*4} Characteristics of built-in transistor

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Grounded emitter propagation

Characteristics

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V_{CE}= 5V

0.1

0.01

0.001

0.001

0.02

0.4

0.6

0.8

1

BASE TO EMITTER VOLTAGE: V_{BE} [V]

Fig.2 Grounded emitter output characteristics 0.9mA 600 0.8mA Ta=25°C 0.7mA 0.6mA 0.5mA 400 0.4mA 0.3mA 0.2mA 200 0.1mA 0 0A 2 10

COLLECTOR TO EMITTER VOLTAGE : $V_{CE}\left[V\right]$

Fig.4 Collector-emitter saturation voltage

Fig.3 DC Current gain vs. Collector Current

Toooo VCE = 5V

Ta= 100°C

25°C

40°C

40°C

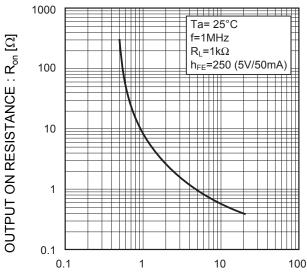
COLLECTOR CURRENT: I_C [mA]

vs. Collector Current 10000 $I_C/I_B=20$ COLLECTOR SATURATION VOLTAGE: V_{CE(sat)} [mV] 1000 100 Ta= 100°C 25°C -40°C 10 0.1 10 100 1000 COLLECTOR CURRENT : I_C [mA]

COLLECTOR CURRENT : I_C [mA]

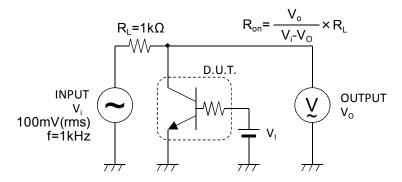
●Electrical characteristic curves(Ta = 25°C)

Fig.5 Output ON resistance vs. input voltage



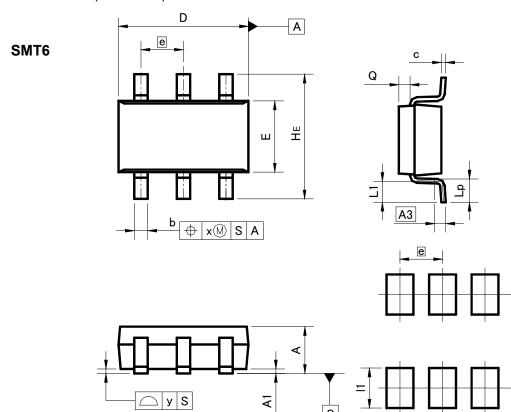
INPUT VOLTAGE: V_I [V]

Fig.6 Ron measurement circuit.



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●Dimensions (Unit : mm)



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Pattern of terminal position areas [Not a recommended pattern of soldering pads]

e1

DIM	MILIM	ETERS	INC	INCHES		
DIM	MIN	MIN MAX		MAX		
Α	1.00	1.30	0.039	0.051		
A1	0.00	0.10	0.000	0.004		
A3	0.5	25	0.0	10		
b	0.25	0.40	0.010	0.016		
С	0.09	0.25	0.004	0.010		
D	2.80	3.00	0.110	0.118		
Е	1.50	1.80	0.059	0.071		
е	0.9	95	0.0	0.037		
HE	2.60	3.00	0.102	0.118		
L1	0.30	0.60	0.012	0.024		
Lp	0.40	0.70	0.016	0.028		
Q	0.20	0.30	0.008	0.012		
х	_	0.20	-	0.008		
У	_	0.10		0.004		

DIM	MILIM	ETERS	INCHES		
DIM	DIM MIN MA		MIN	MAX	
b2		0.60	-	0.024	
e1	2.10 0.083		083		
l1	_	0.90	_	0.035	

Dimension in mm / inches

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